

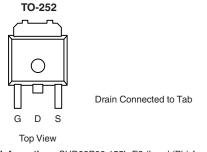
# P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)	
- 60	0.155 at V <sub>GS</sub> = - 10 V	- 8.4	12.5	
	0.280 at V <sub>GS</sub> = - 4.5 V	- 7.4	12.5	

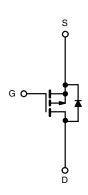
#### **FEATURES**

- TrenchFET® Power MOSFETS
- 175 °C Rated Maximum Junction Temperature





Ordering Information: SUD08P06-155L-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 3$	25 °C, unless othe	rwise noted			
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current (T <sub>.I</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I-	- 8.4		
Continuous Drain Current (1) = 175 G)	T <sub>C</sub> = 100 °C	l <sub>D</sub>	- 6		
Pulsed Drain Current		I <sub>DM</sub>	- 18	Α	
Continuing Source Current (Diode Conduction)		I <sub>S</sub>	- 8.4		
Avalanche Current		I <sub>AS</sub>	- 12		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	7.2	mJ	
Maximum Pawar Dissination	T <sub>C</sub> = 25 °C	P <sub>D</sub>	25 <sup>a</sup>	w	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	r D	2 <sup>b</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
hunding to Ambiguet	t ≤ 10 sec	R <sub>thJA</sub>	20	25	°C/W
Junction-to-Ambient <sup>b</sup>	Steady State		62	75	
Junction-to-Case		R <sub>thJC</sub>	5	6	

#### Notes:

- a. See SOA curve for voltage derating.
- b. Surface Mounted on 1" x 1" FR-4 boad.



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Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit	
Static	- Cyllison	Tool Conditions		.,,,,	mux	- Cinc	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.0	- 2.0	- 3.0		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	-	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1		
	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50	μΑ	
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			- 150	-	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V	- 10			Α	
	( ,	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A		0.125	0.155	Ω	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A, T <sub>J</sub> = 125 °C			0.280		
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A, T <sub>J</sub> = 175 °C			0.350		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2 A		0.158	0.280		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5 A		8		S	
Dynamic	<u>.</u>	·		<b>!</b>			
Input Capacitance	C <sub>iss</sub>			450		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		65			
Reverse Transfer Capacitance	C <sub>rss</sub>	1		40			
Total Gate Charge	$Q_g$			12.5	19	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -8.4 \text{ A}$		2.3			
Gate-Drain Charge	$Q_{gd}$	]		3.2			
Gate Resistance	$R_{g}$	f = 1 MHz		8.0		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			5	10		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 3.57 $\Omega$ $I_D \cong$ - 8.4 A, $V_{GEN}$ = - 10 V, $R_G$ = 2.5 $\Omega$		14	25	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			15	25		
Fall Time <sup>c</sup>	t <sub>f</sub>	1		7	12		
Source-Drain Diode Ratings and Cha	racteristics	(T <sub>C</sub> = 25 °C) <sup>b</sup>		1	<u> </u>		
Pulsed Current	I <sub>SM</sub>				- 20	Α	
Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>F</sub> = - 2 A, V <sub>GS</sub> = 0 V		- 0.9	- 1.3	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 8 A, di/dt = 100 A/μs		50	80	ns	
Reverse Recovery Time	Q <sub>rr</sub>	- i <sub>F</sub> = - ο A, αι/αι = 100 A/μS		80	120	nC	

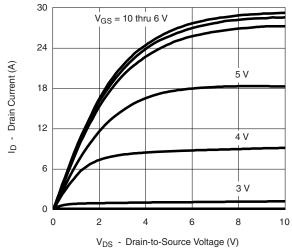
### Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

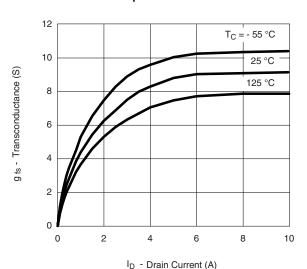
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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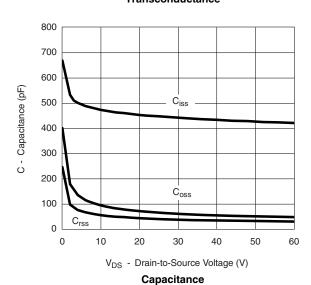
#### TYPICAL CHARACTERISTICS 25 °C unless noted



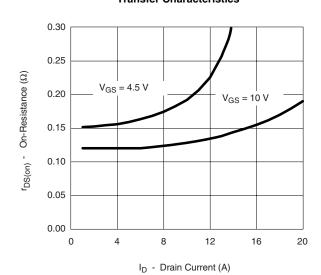
Output Characteristics



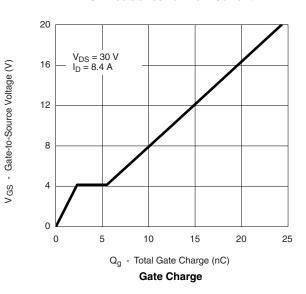
Transconductance



V<sub>GS</sub> - Gate-to-Source Voltage (V) **Transfer Characteristics** 

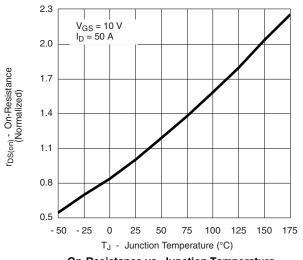


On-Resistance vs. Drain Current

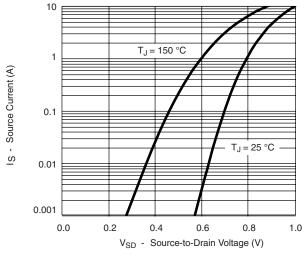


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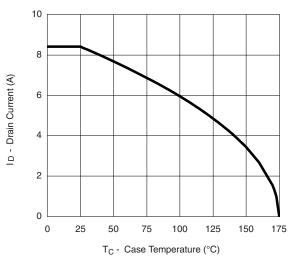


On-Resistance vs. Junction Temperature

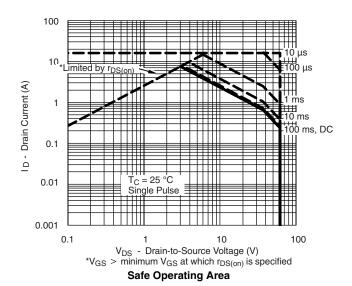


Source-Drain Diode Forward Voltage

#### THERMAL RATINGS



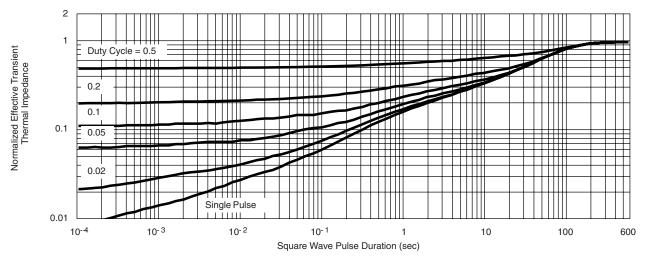
**Drain Current vs. Case Temperature** 



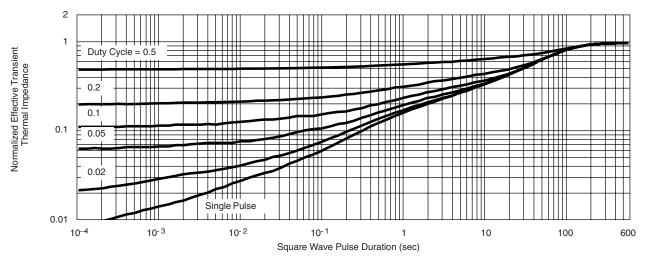
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#### THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



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